

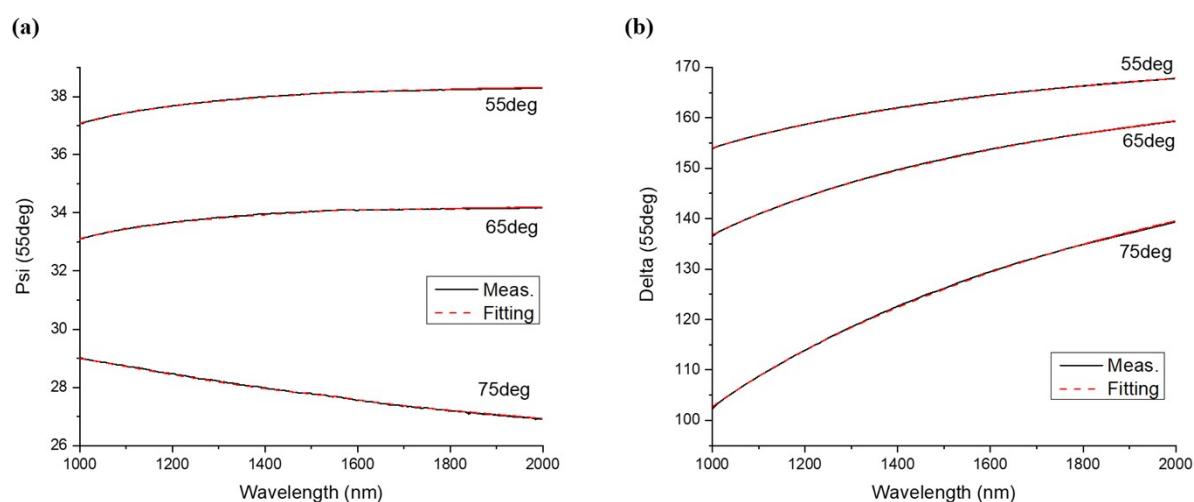
Supporting information for

## Flexible TiN/Ge photodetectors with enhanced responsivity via localized surface plasmon resonance and strain modulation

You Jin Kim<sup>1,†</sup>, Shu An<sup>1,†</sup>, Yikai Liao<sup>1</sup>, Po-Rei Huang<sup>2</sup>, Bongkwon Son<sup>1</sup>, Chuan Seng Tan<sup>1</sup>, Guo-En Chang<sup>2</sup>, and Munho Kim<sup>1,\*</sup>

<sup>1</sup>School of Electrical and Electronic Engineering, Nanyang Technological University, 50 Nanyang Avenue, 639798 Singapore, Singapore

<sup>2</sup>Department of Mechanical Engineering, and Advanced Institute of Manufacturing with High-Tech Innovations (AIM-HI), National Chung Cheng University, Chiayi 62102, Taiwan



**Figure S1.** Measured and fitted (a) amplitude ratio ( $\psi$ ) and (b) phase difference ( $\Delta$ ) of TiN.